N-channel enhancement mode vertical D-MOS transistor

BSP122

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

DESCRIPTION

N-channel enhancement mode vertical D-MOS transistor in a SOT223 envelope and intended for use as a line current interruptor in telephone sets and for applications in relay, high-speed and line transformer drivers.

PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	drain-source voltage	200	V
I_D	DC drain current	550	mA
$R_{DS(on)}$	drain-source on-resistance	2.5	Ω
$V_{GS(th)}$	gate-source threshold voltage	2	V

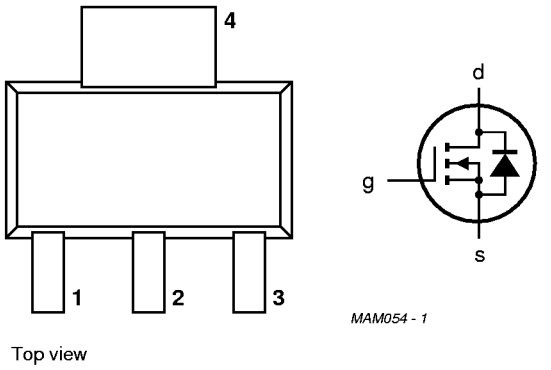

Fig.1 Simplified outline (SOT223) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	200	V
$\pm V_{GSO}$	gate-source voltage	open drain	–	20	V
I_D	DC drain current		–	550	mA
I_{DM}	peak drain current		–	3	A
P_{tot}	total power dissipation	up to T_{amb} = 25 °C (note 1)	–	1.5	W
T_{stg}	storage temperature range		–65	150	°C
T_j	junction temperature		–	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	THERMAL RESISTANCE
$R_{th\ j\text{-}a}$	from junction to ambient (note 1)	83.3 K/W

Note

1. Device mounted on an epoxy printed circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain tab minimum 6 cm^2.

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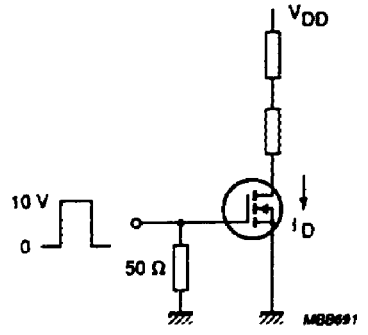
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 10 μA; V_{GS} = 0	200	–	–	V
I_{DSS}	drain-source leakage current	V_{DS} = 160 V; V_{GS} = 0	–	–	1	μA
$\pm I_{GSS}$	gate-source leakage current	$\pm V_{GS}$ = 20 V; V_{DS} = 0	–	–	100	nA
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{GS} = V_{DS}	0.4	–	2	V
$R_{DS(on)}$	drain-source on-resistance	I_D = 750 mA; V_{GS} = 10 V	–	1.6	2.5	Ω
		I_D = 20 mA; V_{GS} = 2.4 V	–	2.5	–	Ω
$\|Y_{fs}\|$	transfer admittance	I_D = 750 mA; V_{DS} = 25 V	400	800	–	mS
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0; f = 1 MHz	–	165	–	pF
C_{oss}	output capacitance	V_{DS} = 25 V; V_{GS} = 0; f = 1 MHz	–	40	–	pF
C_{rss}	feedback capacitance	V_{DS} = 25 V; V_{GS} = 0; f = 1 MHz	–	9	–	pF
Switching times (see Figs 2 and 3)						
t_{on}	turn-on time	I_D = 750 mA; V_{DD} = 50 V; V_{GS} = 0 to 10 V	–	–	35	ns
t_{off}	turn-off time	I_D = 750 mA; V_{DD} = 50 V; V_{GS} = 0 to 10 V	–	–	50	ns



V_{DD} = 50 V.

Fig.2 Switching times test circuit.

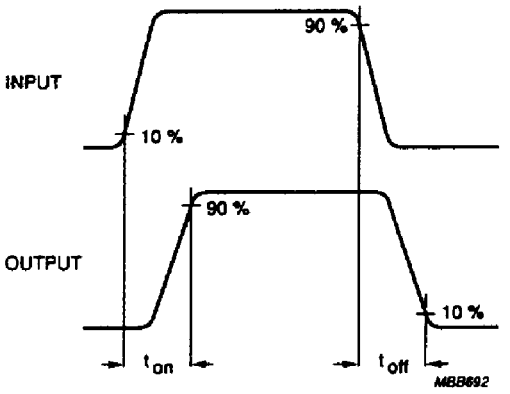
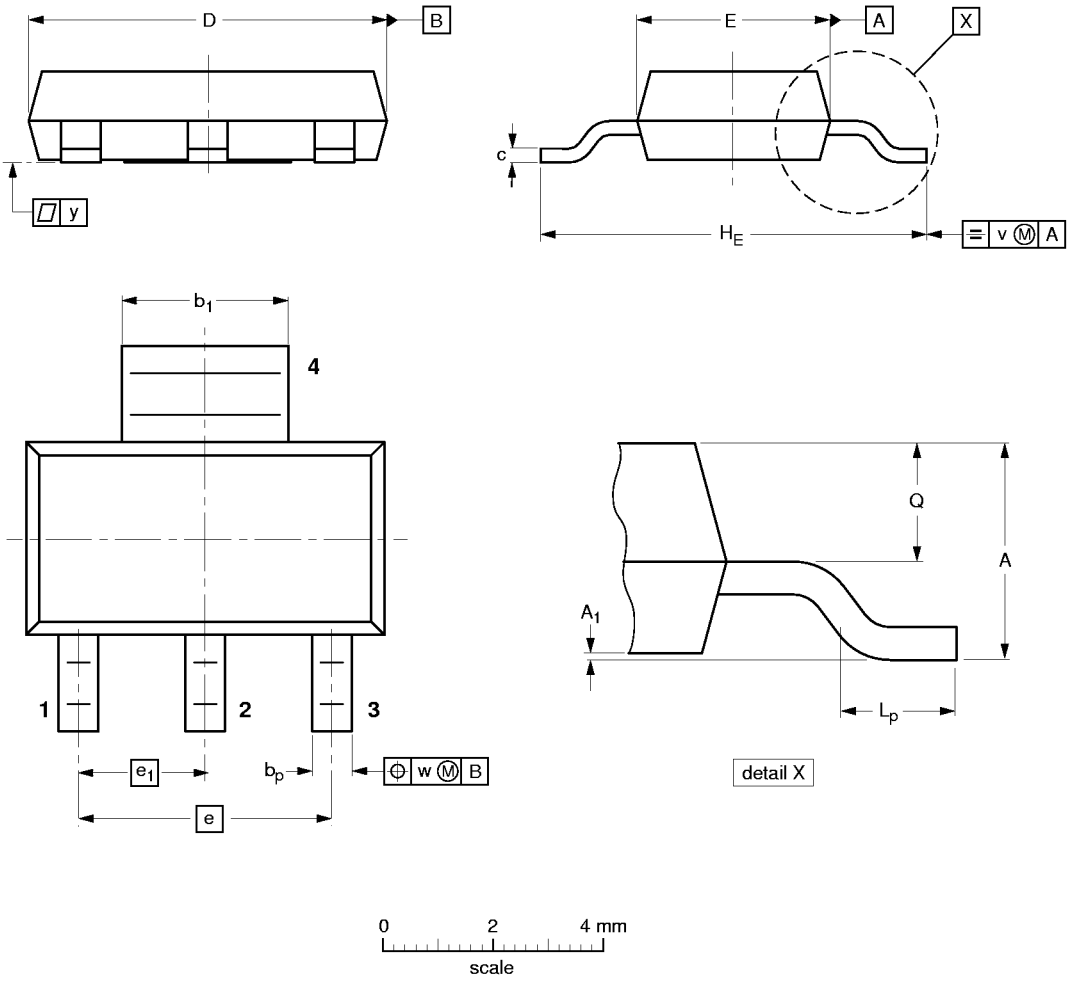


Fig.3 Input and output waveforms.

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223						~~96-11-11~~ 97-02-28